

Notice of References CitedApplication No.
09/116,138Applicant(s)
Anthony et al.Examiner
Bernard SouwGroup Art Unit
2814

Page 1 of 3

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	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS
A	5,834,353	11/10/98	Wu	438	287
B	5,098,623	03/24/92	Pompe	264	65
C	4,432,035	02/14/84	Hsieh et al.	361	322
D	5,923,056	07/13/99	Lee et al.	257	192
E	5,773,325	06/30/98	Teramoto	438	151
F	5,874,766	02/23/99	Hori	257	411
G	5,504,041	04/02/96	Summerfelt	438	396
H	5,876,788	03/02/99	Bronner et al.	427	81
I	5,851,896	12/22/98	Summerfelt	438	396
J	5,187,636	02/16/93	Nakao	361	313
K	5,173,835	12/22/92	Cornett et al.	257	310
L	5,621,681	04/15/97	Moon	365	145
M	5,528,068	06/18/96	Ohmi	257	410

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U	Manchanda et al., "Gate quality doped high K films for CMOS beyond 100 nm: 3-10 nm Al ₂ O ₃ with low leakage and low interface states", IEEE Electron Devices Meeting, IEDM '98 Technical Digest, p.605-608	12/9/98
V	Shimada et al., "Current drive enhancement by using high-permittivity gate insulator in SOI MOSFET's and its limitation", IEEE Trans. El. Devices, 43/3, 1996, pp. 431-435	3/96
W	Shimada et al., "Minimum parasitic resistance for ultra-thin SOI MOSFET with high-permittivity gate insulator performed by lateral contact structure", Proc. 1995 IEEE International SOI Conference, pp. 98-99	10/5/95
X	Chatterjee et al., "CMOS metal replacement gate transistors using tantalum pentoxide gate insulator", IEEE Electron Device Meeting, IEDM '98 Technical Digest, pp. 777-780	12/9/98

Notice of References CitedApplication No.
09/116,138Applicant(s)
Anthony et al.Examiner
Bernard SouwGroup Art Unit
2814

Page 2 of 3

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	B	5,880,006	03/09/99	Lin et al.	438	424
	C	5,851,921	12/22/98	Gardner et al.	438	655
	D	4,227,944	10/14/80	Brown et al.	148	6
	E	4,952,992	08/28/90	Blanchard	357	23.4
	F	5,053,917	10/01/91	Miyasaka et al.	361	321
	G	5,686,748	11/11/97	Thakur et al.	257	310
	H	5,227,320	07/13/93	Johnson et al.	438	304
	I	5,182,232	01/26/93	Chhabra et al.	438	398
	J	4,328,082	05/04/82	Neti et al.	204	195G
	K	3,875,476	04/01/75	Crandall et al.	F23q 7	10
	L	4,060,710	11/29/77	Reuter et al.	219	548
	M	4,054,989	10/25/77	Ho et al.	29	571

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	V	Tseng et al., "Reduced gate leakage current and boron penetration of 0.18 um 1.5 V MOSFETs using integrated RTCVD Oxynitride gate dielectric", IEEE Electron Devices Meeting, IEDM '98 Technical Digest, pp.793-796	12/9/98
	W	Liu, "Circuit requirement and integration challenges of thin gate dielectrics for ultra small MOSFETs", IEEE Electron Devices Meeting, IEDM '98 Technical Digest, pp.747-750	12/9/98
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Notice of References CitedApplication No.
09/116,138Applicant(s)
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Bernard SouwGroup Art Unit
2814

Page 3 of 3

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D					
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F					
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